# LDO Voltage Regulator -Capacitor Free, Low Noise

The NCP140 is a 150 mA very low dropout regulator which offers excellent voltage accuracy and clean output voltage for power sensitive application. The NCP140 is very suitable for battery powered application due to very low quiescent current and virtually zero current at disable mode. This device is stable with or without output capacitors and allows minimize footprint and BOM. The XDFN4 package is optimized for use in space constrained applications.

#### Features

- Stable Operation with or without Capacitors
- Operating Input Voltage Range: 1.6 V to 5.5 V
- Available in Fixed Voltage Options: 1.5 V to 5 V Contact Factory for Other Voltage Options
- ±1% Typical Accuracy @ 25°C
- Very Low Quiescent Current of Typ. 45 μA
- Standby Current: 0.1 µA
- Very Low Dropout: 125 mV for 3.3 V @ 150 mA
- High PSRR: 55 dB @ 1 kHz
- Available in XDFN4 0.8 mm x 0.8 mm x 0.4 mm Package - XDFN4 - 1.0 mm x 1.0 mm x 0.4 mm Package
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

# **Typical Applications**

- Battery-powered Equipment
- Smartphones, Tablets
- Cameras, DVRs, STB and Camcorders

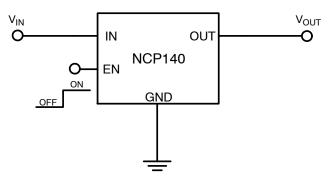
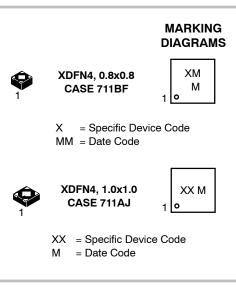


Figure 1. Typical Application Schematic

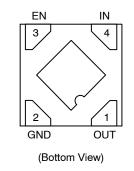


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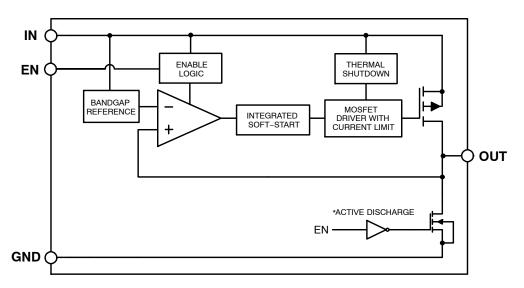


**PIN CONNECTIONS** 



#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 13 of this data sheet.



\*Active output discharge is available only for NCP140Axxx options.

#### Figure 2. Simplified Schematic Block Diagram

Pin No.	Pin Name	Description
1	OUT	Regulated output voltage pin. A small ceramic capacitor can be connected to improve fast load transient.
2	GND	Ground pin
3	EN	Driving EN over 0.9 V turns on the regulator. Driving EN below 0.4 V puts the regulator into shutdown mode.
4	IN	Input pin
-	EPAD	Expose pad must be connect to GND pin as short as possible. Soldered to a large ground copper plane al- lows for effective heat removal.

# **PIN FUNCTION DESCRIPTION**

#### **ABSOLUTE MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Input Voltage (Note 1)	V <sub>IN</sub>	–0.3 V to 6	V
Output Voltage	V <sub>OUT</sub>	–0.3 V to V <sub>IN</sub> + 0.3 V or 6 V	V
Chip Enable Input	V <sub>CE</sub>	–0.3 V to 6 V	V
Output Short Circuit Duration	t <sub>SC</sub>	unlimited	s
Maximum Junction Temperature	TJ	150	°C
Storage Temperature	T <sub>STG</sub>	–55 to 150	°C
ESD Capability, Human Body Model (Note 2)	ESD <sub>HBM</sub>	2000	V
ESD Capability, Machine Model (Note 2)	ESD <sub>MM</sub>	200	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.

2. This device series incorporates ESD protection and is tested by the following methods:

ESD Human Body Model tested per EIA/JESD22-A114

ESD Machine Model tested per EIA/JESD22-A115

Latchup Current Maximum Rating tested per JEDEC standard: JESD78.

#### THERMAL CHARACTERISTICS

Rating		Value	Unit
Thermal Characteristics, XDFN4 0.8 mm x 0.8 mm Thermal Resistance, Junction-to-Air (Note 3)	$R_{\thetaJA}$	252	°C/W
Thermal Characteristics, XDFN4 1.0 mm x 1.0 mm Thermal Resistance, Junction-to-Air (Note 3)	$R_{\thetaJA}$	265	°C/W

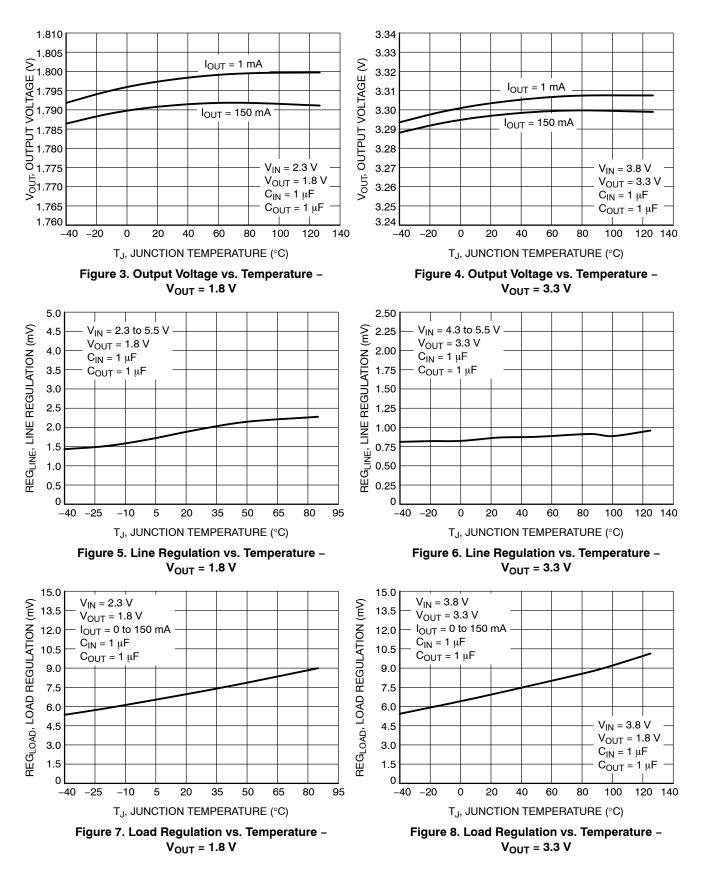
3. Measured according to JEDEC board specification. Detailed description of the board can be found in JESD51-7

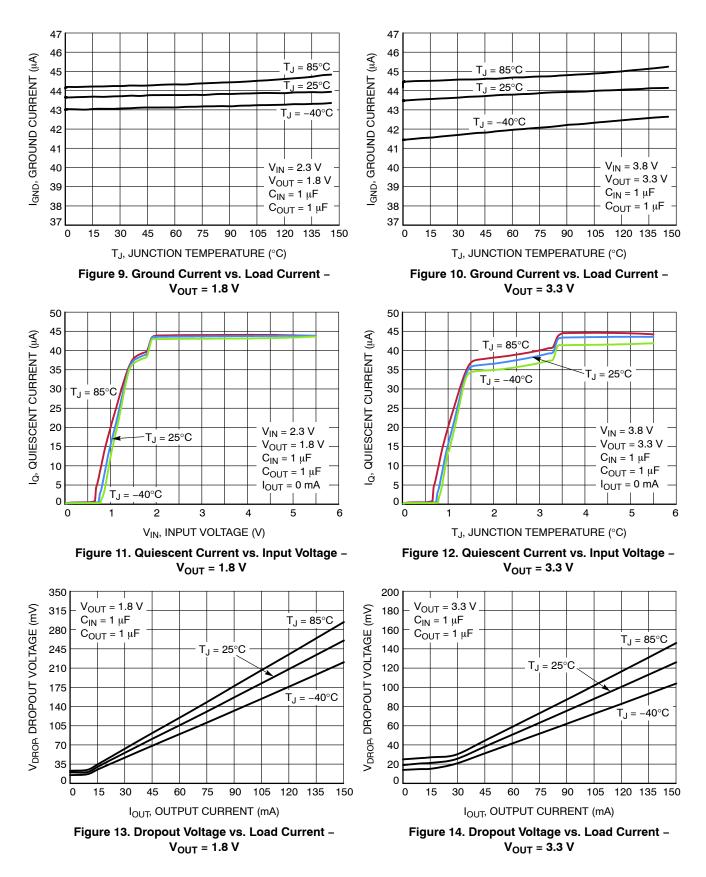
Parameter	Test Conditio	Test Conditions		Min	Тур.	Max	Unit
Operating Input Voltage			V <sub>IN</sub>	1.6		5.5	V
Output Voltage Accuracy	V <sub>OUT</sub> ≥ 1.8 V, T <sub>J</sub> :	$V_{OUT} \ge 1.8 \text{ V}, \text{ T}_{\text{J}} = 25^{\circ}\text{C}$			±1		%
	V <sub>OUT</sub> < 1.8 V, T <sub>J</sub> :	V <sub>OUT</sub> < 1.8 V, T <sub>J</sub> = 25°C			±20		mV
	V <sub>OUT</sub> ≥ 1.8 V, –40°C ≤	$V_{OUT} \ge 1.8 \text{ V}, -40^{\circ}\text{C} \le T_J \le 85^{\circ}\text{C}$		-2		+2	%
	V <sub>OUT</sub> < 1.8 V, −40°C ≤	≤ T <sub>J</sub> ≤ 85°C		-50		+50	mV
Line Regulation	V <sub>OUT(NOM)</sub> + 0.5 V ≤ V	V <sub>IN</sub> ≤ 5.5 V	Line <sub>Reg</sub>		1.0	5.0	mV
Load Regulation	I <sub>OUT</sub> = 0 mA to 1	50 mA	Load <sub>Reg</sub>		10	30	mV
Dropout Voltage (Note 5)	450	V <sub>OUT(NOM)</sub> = 1.8 V	V <sub>DO</sub>		255	390	mV
	I <sub>OUT</sub> = 150 mA	V <sub>OUT(NOM)</sub> = 3.3 V			125	220	
Output Current Limit	V <sub>OUT</sub> = 90% V <sub>OU</sub>	T(NOM)	I <sub>CL</sub>		230		mA
Short Circuit Current	V <sub>OUT</sub> = 0V	V <sub>OUT</sub> = 0V			250		mA
Quiescent Current	I <sub>OUT</sub> = 0 mA	I <sub>OUT</sub> = 0 mA			45	75	μΑ
Shutdown Current	$V_{EN} \le 0.4 \text{ V}, \text{ V}_{IN} =$	$V_{EN} \le 0.4$ V, $V_{IN} = 5.5$ V			0.1	1.0	μΑ
EN Pin Threshold Voltage	EN Input Voltage "H"		V <sub>ENH</sub>	0.9			V
	EN Input Voltage "L"		V <sub>ENL</sub>			0.4	1
EN Pin Current	V <sub>EN</sub> = 5.5 V	V <sub>EN</sub> = 5.5 V			0.01	1.0	μΑ
Turn–On Time	$C_{OUT}$ = 1 µF, $I_{OUT}$ = From assertion of V <sub>EN</sub> to V <sub>OU</sub>	$C_{OUT}$ = 1 $\mu$ F, I <sub>OUT</sub> =150 mA, From assertion of V <sub>EN</sub> to V <sub>OUT</sub> = 98%V <sub>OUT(NOM)</sub>			100		μs
Power Supply Rejection Ratio	V <sub>IN</sub> = 3.5 V, V <sub>OUT(NOM)</sub> = 2.5 V,	f = 100 Hz	PSRR	62		dB	
	$I_{OUT} = 10 \text{ mA}$	f = 1 kHz			55		
Output Noise Voltage	V <sub>IN</sub> = 2.3 V, V <sub>OUT(NOM)</sub> = 1.8 V, I <sub>OUT</sub> = 10 mA f = 100 Hz to 100 kHz		V <sub>N</sub>		17		μV <sub>RMS</sub>
Thermal Shutdown Temperature	r Temperature Temperature increasing from T <sub>J</sub> = +25°C		T <sub>SD</sub>		160		°C
Thermal Shutdown Hysteresis	Temperature falling from T <sub>SD</sub>		T <sub>SDH</sub>		20		°C
Output Discharge Pull-Down	$V_{EN} \le 0.4 V$ , A options only		R <sub>DISCH</sub>		100		Ω

$\textbf{ELECTRICAL CHARACTERISTICS} - 40^{\circ}C \leq T_J \leq 85^{\circ}C; \ V_{IN} = V_{OUT(NOM)} + 0.5 \ V; \ I_{OUT} = 1 \ \text{mA}, \ C_{IN} = C_{OUT} = \text{none, unless}$	
otherwise noted. V <sub>EN</sub> = 0.9 V. Typical values are at $T_J$ = +25°C. Min/Max values are for $-40°C \le T_J \le 85°C$ (Note 3)	

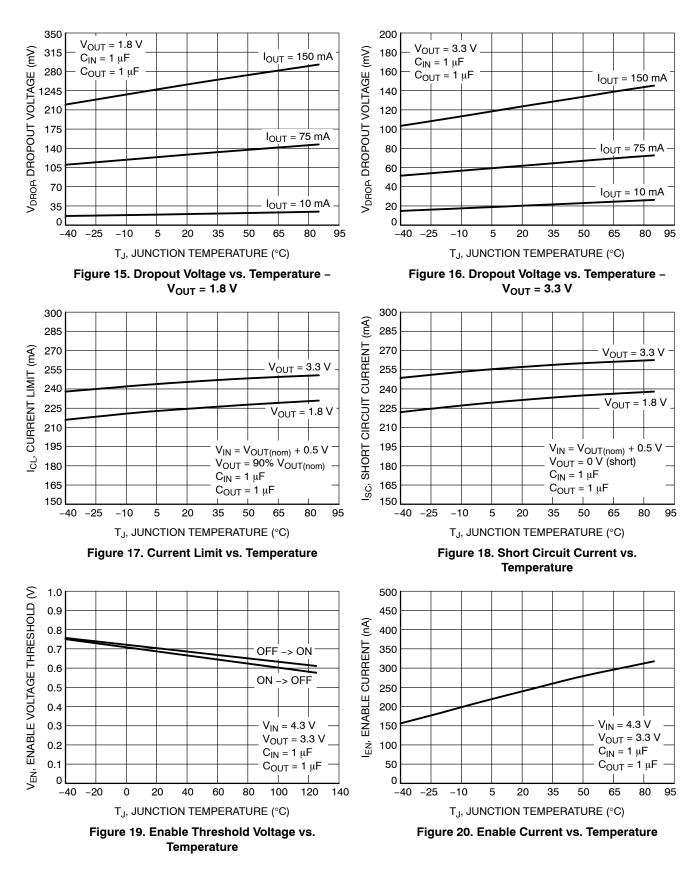
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product

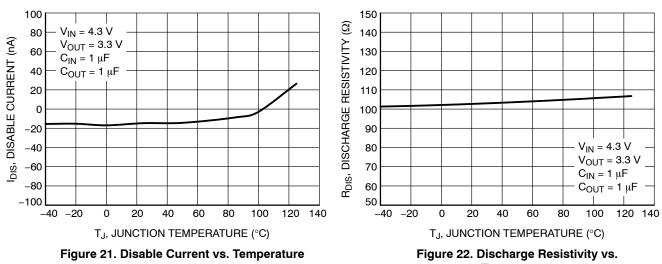
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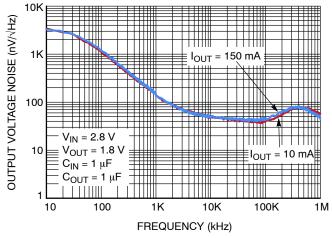






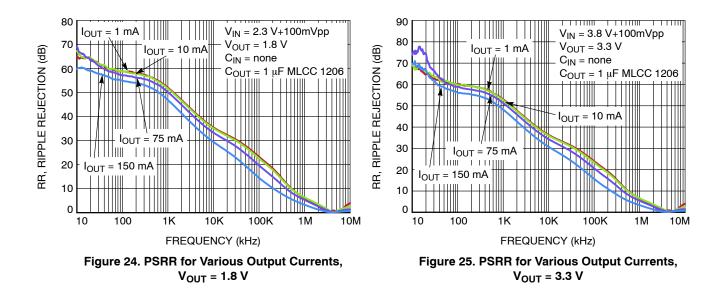


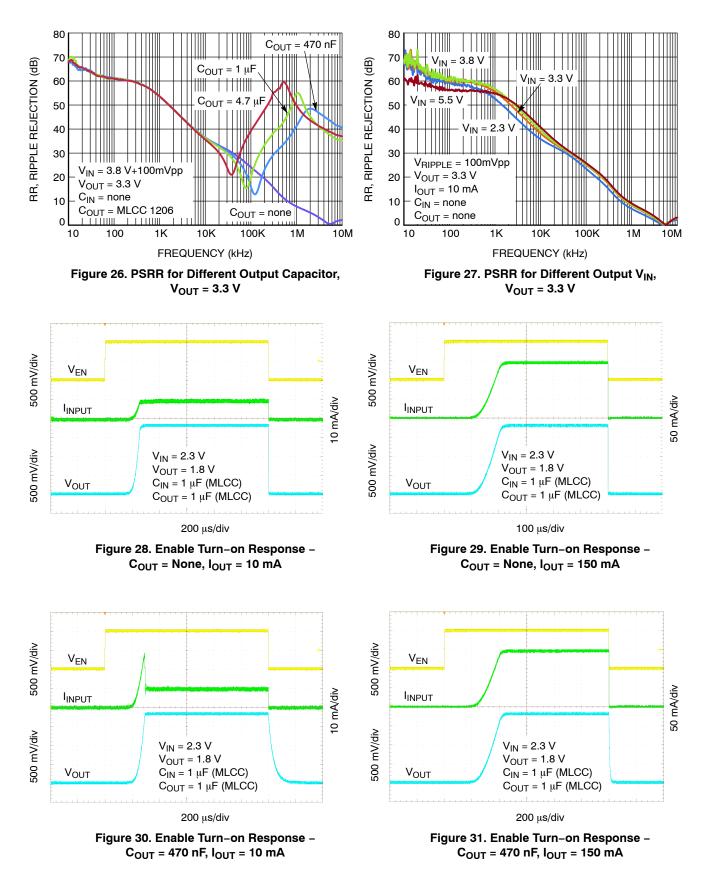
Temperature

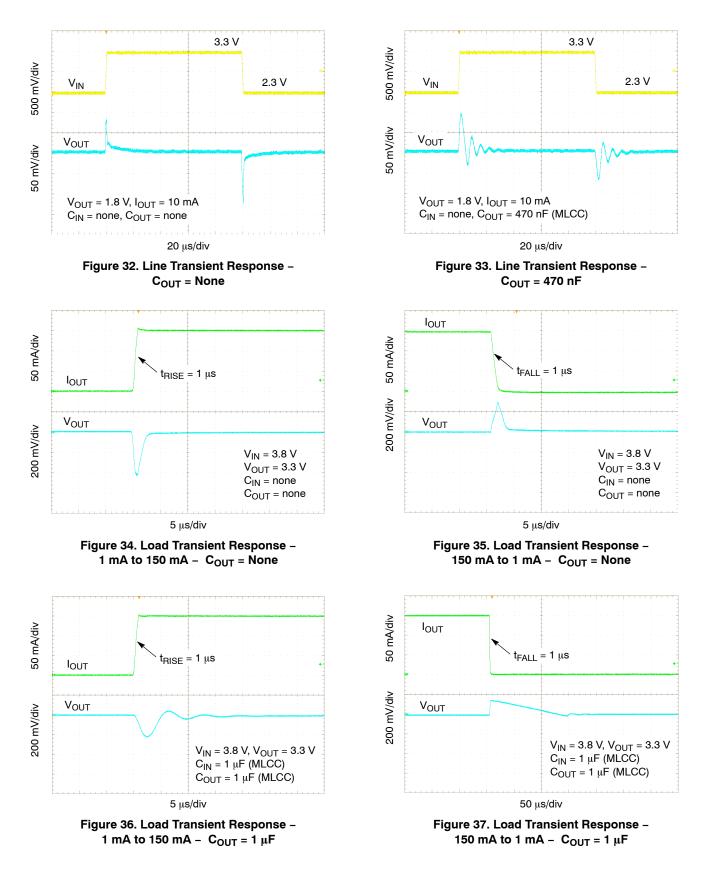


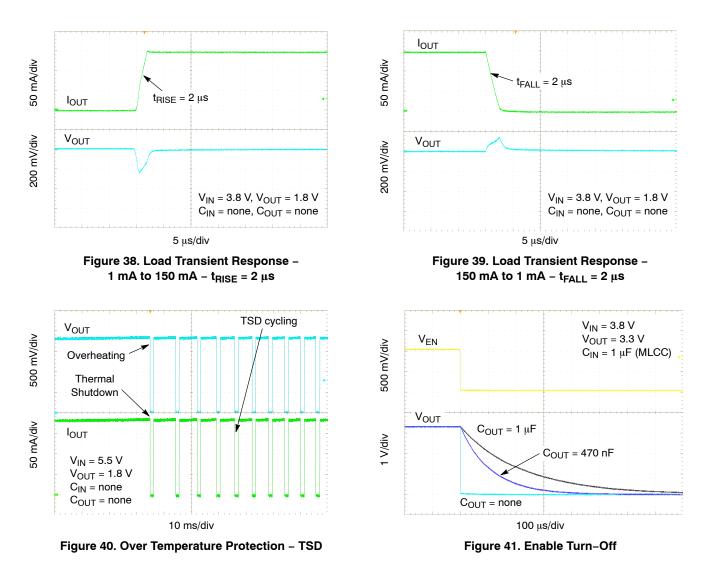
	RMS Output Noise (μV)			
l <sub>оит</sub>	10 Hz – 100 kHz	100 Hz – 100 kHz		
10 mA	26.21	17.94		
150 mA	27.51	19.11		











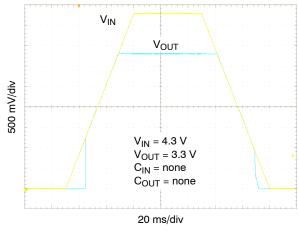


Figure 42. Slow V<sub>IN</sub> Ramp

#### APPLICATIONS INFORMATION

#### General

The NCP140 is high performance low dropout regulator capable of supplying 150 mA and providing very stable output voltage with or without capacitors. The device is designed to remain stable with any type of capacitor or even without input and output capacitor. The NCP140 also offers low quiescent current and very small packages suitable for space constrains application. In connection with no capacitor requirements the regulator is very useful in wearable application, smartphones and everywhere where is high power density required.

#### Input and Output Capacitor Selection

In spite of the NCP140 is designed as capless device capacitors can be added to improve dynamic behavior such as fast load transient or PSRR. Recommendation for selection input and output capacitor is very similar as for high performance LDO. Low ESR ceramic capacitor is the most beneficial for improvement load transient and PSRR but suitable is almost any type of capacitor. The NCP140 remains stable with electrolytic and tantalum capacitor too.

#### **Enable Operation**

The NCP140 uses the EN pin to enable/disable its device and to deactivate/activate the active discharge function.

If the EN pin voltage is <0.4 V the device is guaranteed to be disabled. The pass transistor is turned–off so that there is virtually no current flow between the IN and OUT. The active discharge transistor is active (only A option) so that the output voltage V<sub>OUT</sub> is pulled to GND through a 100  $\Omega$ resistor. In the disable state the device consumes as low as typ. 10 nA from the V<sub>IN</sub>.

If the EN pin voltage >0.9 V the device is guaranteed to be enabled. The NCP140 regulates the output voltage and the active discharge transistor is turned-off.

The EN pin has internal pull-down current source with typ. value of 100 nA which assures that the device is turned-off when the EN pin is not connected. In the case where the EN function isn't required the EN should be tied directly to IN.

#### **Output Current Limit**

Output Current is internally limited within the IC to a typical 230 mA. The NCP140 will source this amount of current measured with a voltage drops on the 90% of the nominal  $V_{OUT}$ . If the Output Voltage is directly shorted to ground ( $V_{OUT} = 0$  V), the short circuit protection will limit the output current to approximately 250 mA. The current limit and short circuit protection will work properly over whole temperature range and also input voltage range. There is no limitation for the short circuit duration.

#### Thermal Shutdown

When the die temperature exceeds the Thermal Shutdown threshold ( $T_{SD} - 160^{\circ}$ C typical), Thermal Shutdown event is detected and the device is disabled. The IC will remain in this state until the die temperature decreases below the Thermal Shutdown Reset threshold ( $T_{SDU} - 140^{\circ}$ C typical). Once the IC temperature falls below the 140°C the LDO is enabled again. The thermal shutdown feature provides the protection from a catastrophic device failure due to accidental overheating. This protection is not intended to be used as a substitute for proper heat sinking.

#### **Power Dissipation**

As power dissipated in the NCP140 increases, it might become necessary to provide some thermal relief. The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part.

The maximum power dissipation the NCP140 can handle is given by:

$$P_{D(MAX)} = \frac{\left[85^{\circ}C - T_{A}\right]}{\theta_{JA}}$$
 (eq. 1)

The power dissipated by the NCP140 for given application conditions can be calculated from the following equation:

$$\mathsf{P}_\mathsf{D} \approx \mathsf{V}_\mathsf{IN} \big( \mathsf{I}_\mathsf{GND} @ \mathsf{I}_\mathsf{OUT} \big) + \mathsf{I}_\mathsf{OUT} \big( \mathsf{V}_\mathsf{IN} - \mathsf{V}_\mathsf{OUT} \big) \quad \text{(eq. 2)}$$

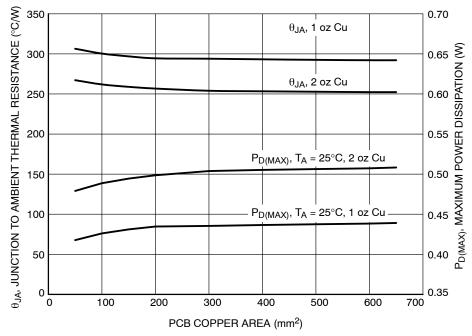


Figure 43.  $\theta_{JA}$  and P<sub>D (MAX)</sub> vs. Copper Area (XDFN4– 0.8 x 0.8 mm)

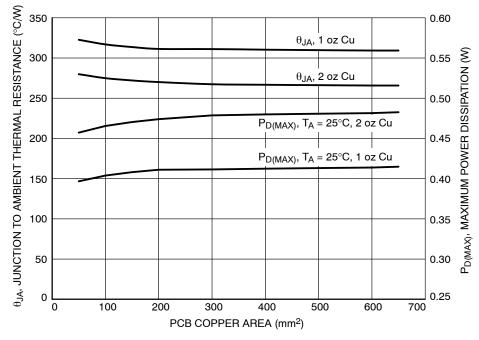


Figure 44.  $\theta_{JA}$  and P<sub>D (MAX)</sub> vs. Copper Area (XDFN4– 1 x 1 mm)

#### **Reverse Current**

The PMOS pass transistor has an inherent body diode which will be forward biased in the case that  $V_{OUT} > V_{IN}$ . Due to this fact in cases, where the extended reverse current condition can be anticipated the device may require additional external protection.

#### Turn-On Time

The turn–on time is defined as the time period from EN assertion to the point in which  $V_{OUT}$  will reach 98% of its

nominal value. This time is dependent on various application conditions such as  $V_{OUT(NOM)}$ ,  $C_{OUT}$ ,  $T_A$ .

#### **PCB Layout Recommendations**

Larger copper area connected to the pins will improve the device thermal resistance and improve maximum power dissipation. The actual power dissipation can be calculated from the equation above (Equation 2). Expose pad should be tied the shortest path to the GND pin.

# **ORDERING INFORMATION**

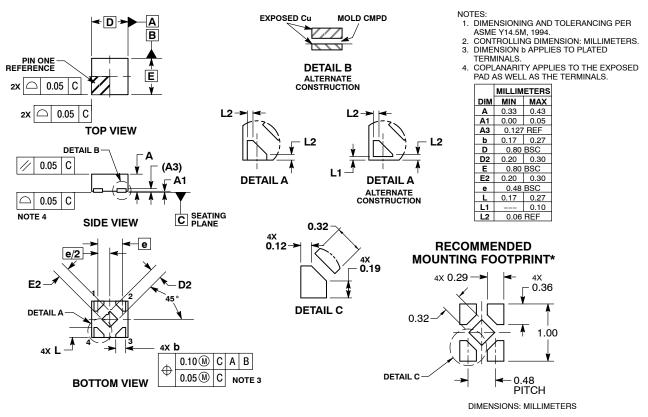
Device	Nominal Output Voltage	Description	Marking	Package	Shipping <sup>†</sup>	
NCP140AMXC180TCG	1.8 V		GA			
NCP140AMXC280TCG	2.8 V		GC			
NCP140AMXC300TCG	3.0 V	Active Output Discharge	GE	XDFN4 (Pb-Free)	3000 / Tape & Reel	
NCP140AMXC330TCG	3.3 V		GD	CASE 711BF		
NCP140BMXC330TCG	3.3 V	Without Active Output Discharge	G2			
NCP140AMXD180TCG	1.8 V		GA			
NCP140AMXD280TCG	2.8 V	Active Output Discharge	GC	XDFN4		
NCP140AMXD300TCG	3.0 V		GE	(Pb-Free)	3000 / Tape & Reel	
NCP140AMXD330TCG	3.3 V		GD	CASE 711AJ		
NCP140BMXD330TCG	3.3 V	Without Active Output Discharge	G2			

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

XDFN4 0.8x0.8, 0.48P CASE 711BF

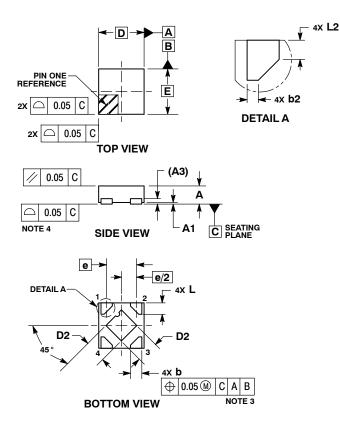




\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

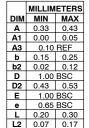
#### PACKAGE DIMENSIONS

XDFN4 1.0x1.0, 0.65P CASE 711AJ **ISSUE A** 

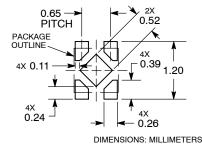


NOTES: DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

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- AGINE 114.30%, 1994. CONTROLLING DIMENSION: MILLIMETERS. DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 mm FROM THE TERMINAL TIPS. 3
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS. 4



#### RECOMMENDED **MOUNTING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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